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May 2014

FDA33N25

N-Channel UniFETTM MOSFET 250 V, 33 A, 94 m Ω

Features

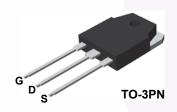
- $R_{DS(on)}$ = 88 $m\Omega$ (Typ.) @ V_{GS} = 10 V, I_D =16.5 A
- · Low Gate Charge (Typ. 36 nC)
- Low C_{rss} (Typ. 35 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

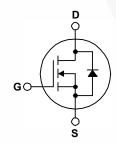
Applications

- PDP TV
- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDA33N25	Unit
V_{DSS}	Drain to Source Voltage			250	V
V_{GSS}	Gate to Source Voltage			±30	V
	Drain Current	- Continuous (T _C = 25°C)		33	А
ID	Drain Current	- Continuous (T _C = 100°C)		21	A
I _{DM}	Drain Current	- Pulsed	(Note 1)	132	Α
E _{AS}	Single Pulsed Avalanche	Energy	(Note 2)	918	mJ
I _{AR}	Avalanche Current		(Note 1)	33	Α
E _{AR}	Repetitive Avalanche En	ergy	(Note 1)	24.6	mJ
dv/dt	Peak Diode Recovery dv	/dt	(Note 3)	4.5	V/ns
D	Dawer Dissination	$(T_C = 25^{\circ}C)$		245	W
P_{D}	Power Dissipation	- Derate Above 25°C		1.96	W/°C
T _J , T _{STG}	Operating and Storage T	emperature Range		-55 to +150	°C
T_L	Maximum Lead Tempera	ture for Soldering, 1/8" from Case for 5 Se	conds	300	°C

Thermal Characteristics

Symbol	Parameter	FDA33N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.51	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDA33N25	FDA33N25	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	250	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C	-	0.34	-	V/°C
1	Zero Gate Voltage Drain Current	$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μA
I _{DSS} Zero Gate voltage L	Zero Gate Voltage Drain Current	$V_{DS} = 200 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μΑ
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 16.5 A	-	0.088	0.094	Ω
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 16.5 A	ı	24.2	1	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05.V.V 0.V	-	1655	2200	pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz	-	315	420	pF
C _{rss}	Reverse Transfer Capacitance	1 = 1 WH 12	-\	35	55	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 200 V, I _D = 33 A,	-	36	46.8	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	10.8	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(No	te 4)	16	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	33	76	ns
t _r		$V_{DD} = 125 \text{ V}, I_D = 33 \text{ A},$	-	142	293	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 25 Ω	- /	77	165	ns
t _f	Turn-Off Fall Time	(Note 4)	- /	68	146	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	33	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	132	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 33 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 33 A,	-	256	-	ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt = 100 A/μs	-	2.3	_	μС

Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 1.35 mH, I_{AS} = 33 A, V_{DD} = 50 V, R_{G} = 25 Ω , starting T_{J} = 25°C.
- 3. $I_{SD} \le 33$ A, di/dt ≤ 200 A/µs, $V_{DD} \le BV_{DSS}$, starting T_J = 25°C.
- 4. Essentially independent of operating temperature typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

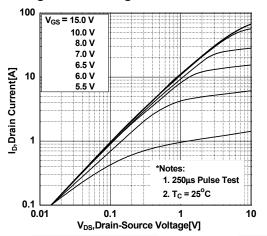


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

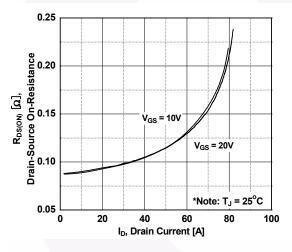


Figure 5. Capacitance Characteristics

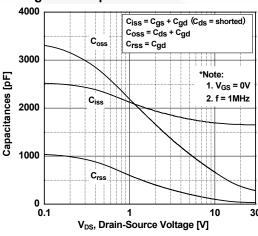


Figure 2. Transfer Characteristics

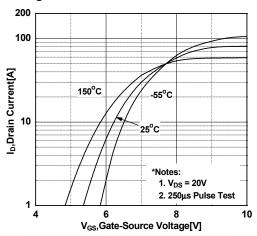


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

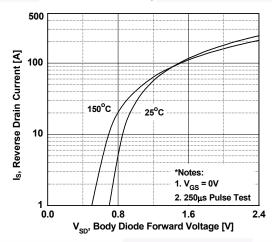
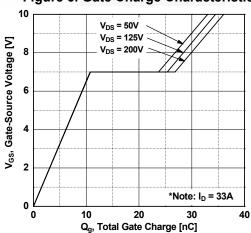


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

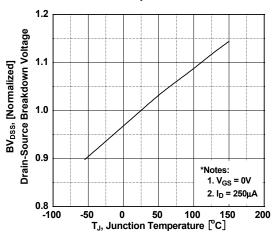


Figure 8. On-Resistance Variation vs. Temperature

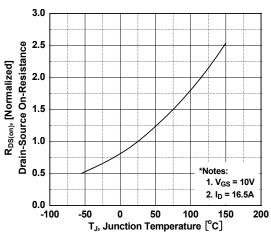


Figure 9. Maximum Safe Operating Area

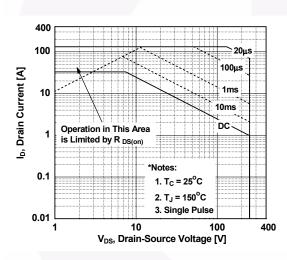


Figure 10. Maximum Drain Current vs. Case Temperature

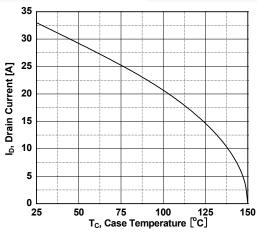
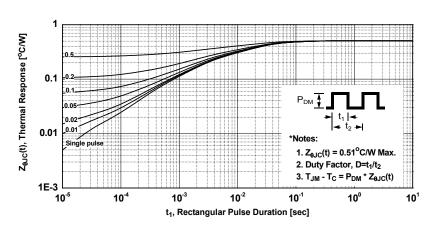


Figure 11. Transient Thermal Response Curve



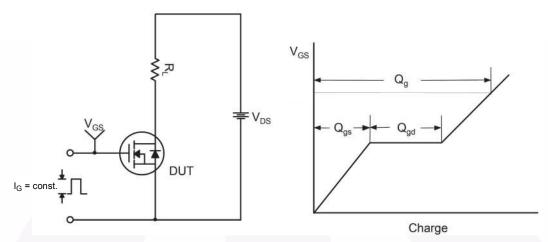


Figure 12. Gate Charge Test Circuit & Waveform

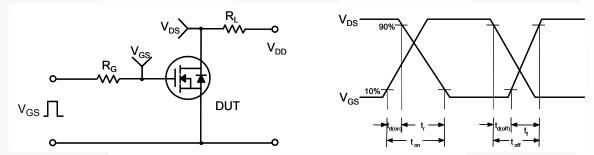


Figure 13. Resistive Switching Test Circuit & Waveforms

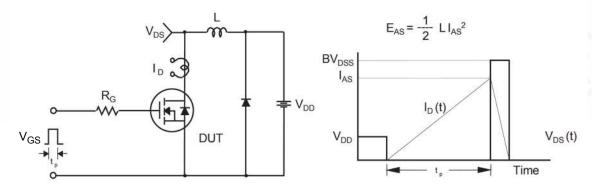


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

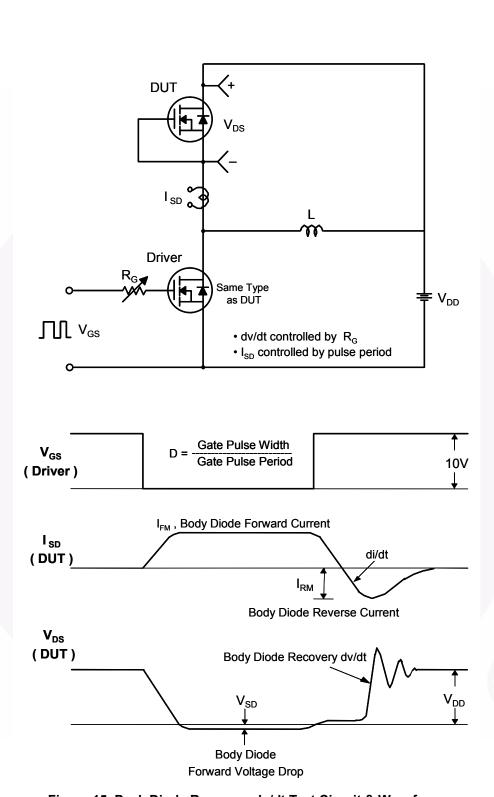


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

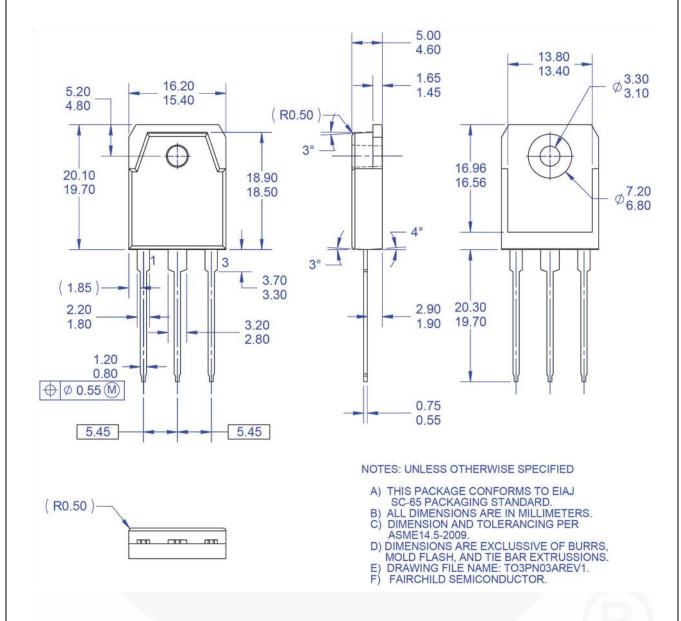


Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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